



ABSTRACT

-- The present invention relates to a A method of manufacturing a semiconductor device, comprising includes the steps of[[:] forming a sunken section in an insulating film formed on a substrate[();] and forming a barrier metal film on [[said]] the insulating film inclusive of [[said]] the sunken section[[;]]. The method also includes forming a copper-based film over the entire surface so as to fill up [[said]] the sunken section[[;]] and forming a copper-based metal interconnection, which comprises the step of. The interconnection is formed by polishing this substrate surface by the chemical mechanical polishing method, using a polishing slurry containing a silica polishing material, an oxidizing agent, an amino acid, a triazole-based compound and water, wherein a. A content ratio of [[said]] the amino acid to [[said]] the triazole-based compound (amino acid / triazole-based compound (weight ratio)) is 5 to 8.--